

## Dual N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
40	0.020 at V <sub>GS</sub> = 10 V	9.2	4.9
	0.023 at V <sub>GS</sub> = 4.5 V	8.6	

### FEATURES

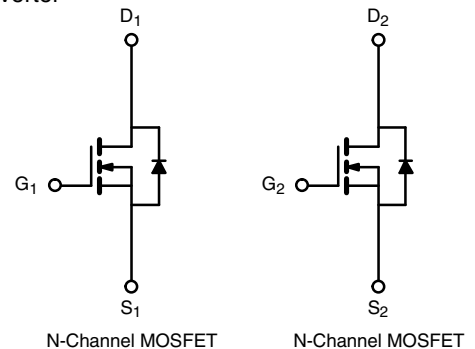
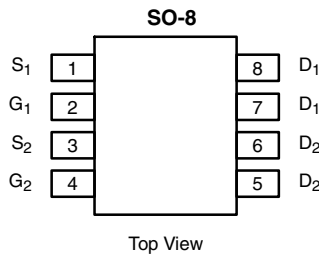
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- CCFL Inverter
- DC/DC Converter
- HDD



Ordering Information: Si4288DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	40	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	9.2	
		T <sub>C</sub> = 70 °C	7.4	
		T <sub>A</sub> = 25 °C	7.4 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	5.9 <sup>b, c</sup>	
Pulsed Drain Current (10 μs Pulse Width)	I <sub>DM</sub>	50	A	
Source-Drain Current Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C		2.6
		T <sub>A</sub> = 25 °C		1.6 <sup>b, c</sup>
Pulsed Source-Drain Current	I <sub>SM</sub>	50		
Single Pulse Avalanche Current	I <sub>AS</sub>	10		
Single Pulse Avalanche Energy	E <sub>AS</sub>	L = 0.1 mH		5
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	3.1	
		T <sub>C</sub> = 70 °C	2	
		T <sub>A</sub> = 25 °C	2 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	1.28 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	49	62.5	°C/W
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	30	40	

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under steady state conditions is 120 °C/W.

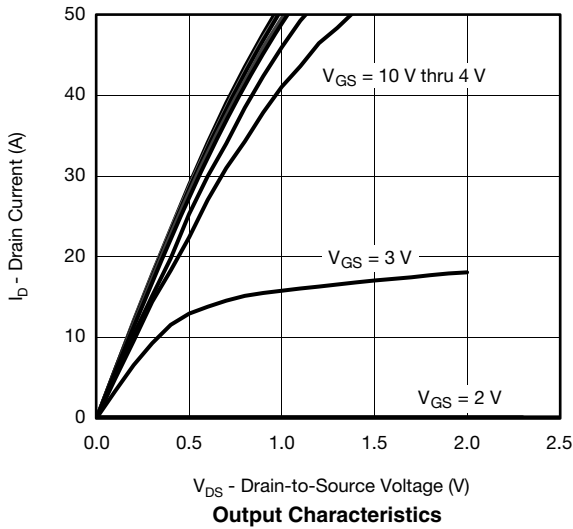
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		49		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-5.2		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.2		2.5	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			100	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance <sup>b</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		0.0165	0.0200	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 7\text{ A}$		0.019	0.023	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 10\text{ A}$		35		S
<b>Dynamic<sup>a</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, I_D = 1\text{ MHz}$		580		pF
Output Capacitance	$C_{oss}$			100		
Reverse Transfer Capacitance	$C_{rss}$			42		
Total Gate Charge	$Q_g$	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		10	15	nC
		$V_{DS} = 20\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$		4.9	7.4	
Gate-Source Charge	$Q_{gs}$			1.5		
Gate-Drain Charge	$Q_{gd}$		1.5			
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	0.6	2.7	5.4	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 2\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		7	14	ns
Rise Time	$t_r$			9	18	
Turn-Off Delay Time	$t_{d(off)}$			16	32	
Fall Time	$t_f$			8	16	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 2\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		12	24	
Rise Time	$t_r$			10	20	
Turn-Off Delay Time	$t_{d(off)}$			13	26	
Fall Time	$t_f$			8	16	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			2.6	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				50	
Body Diode Voltage	$V_{SD}$	$I_S = 3\text{ A}$		0.77	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		15	30	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			7.5	15	nC
Reverse Recovery Fall Time	$t_a$			9		ns
Reverse Recovery Rise Time	$t_b$			6		

## Notes:

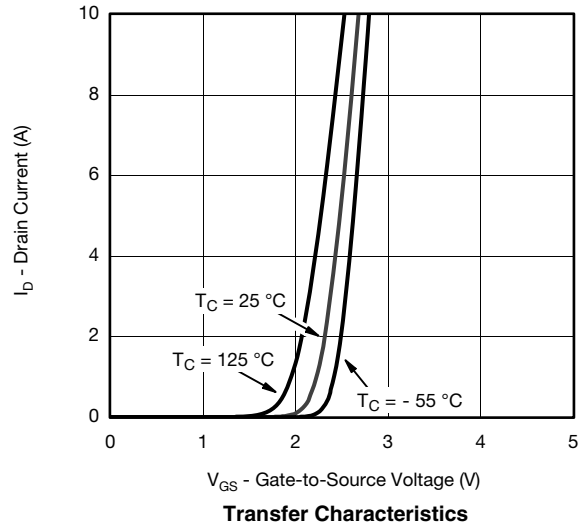
- a. Guaranteed by design, not subject to production testing.  
b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

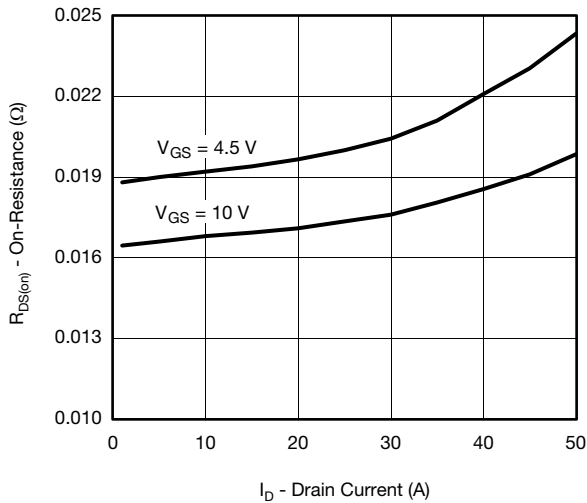
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



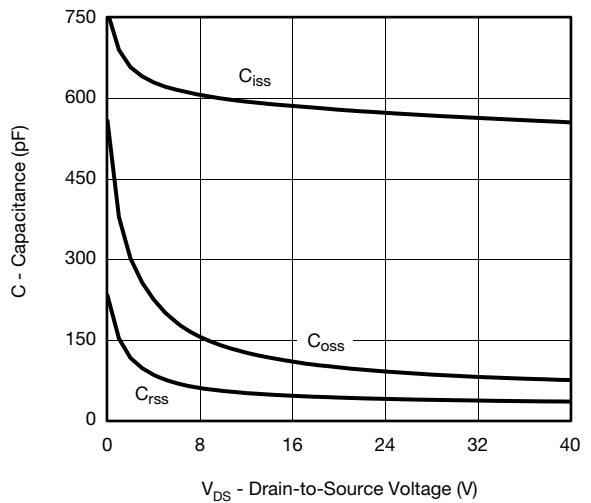
**Output Characteristics**



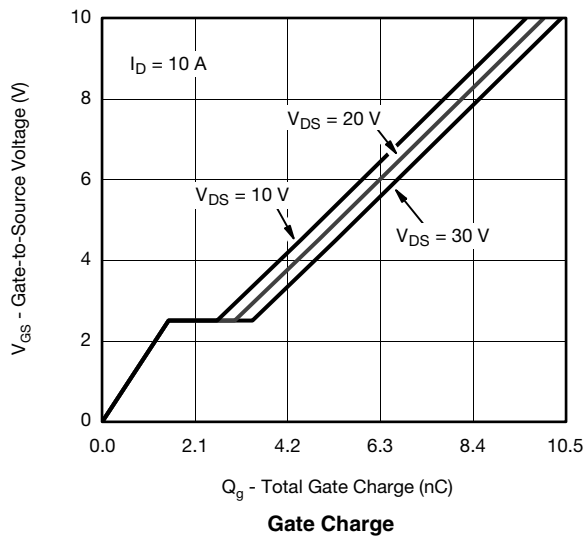
**Transfer Characteristics**



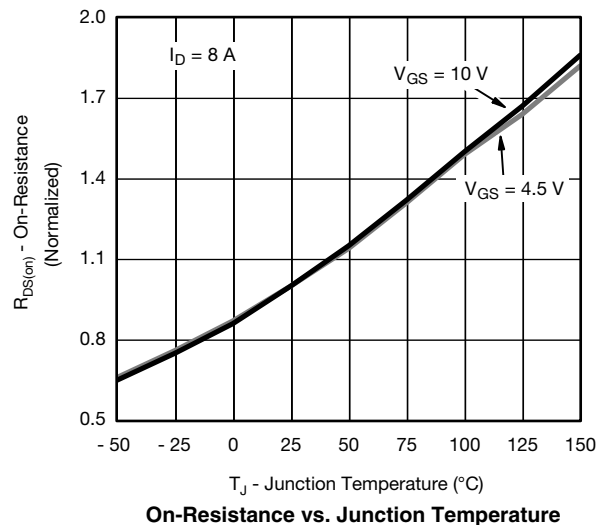
**On-Resistance vs. Drain Current**



**Capacitance**

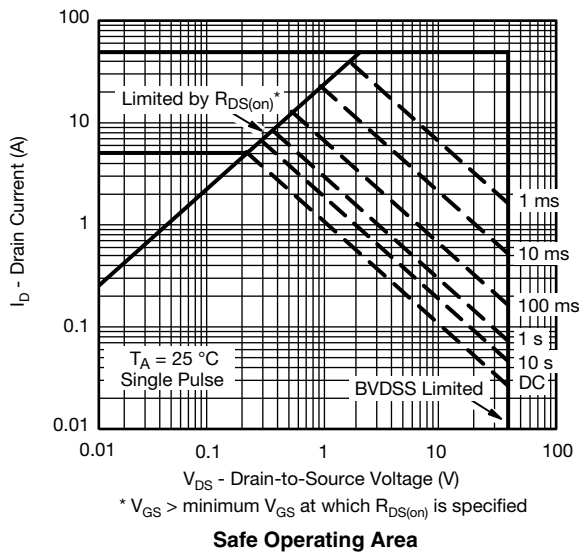
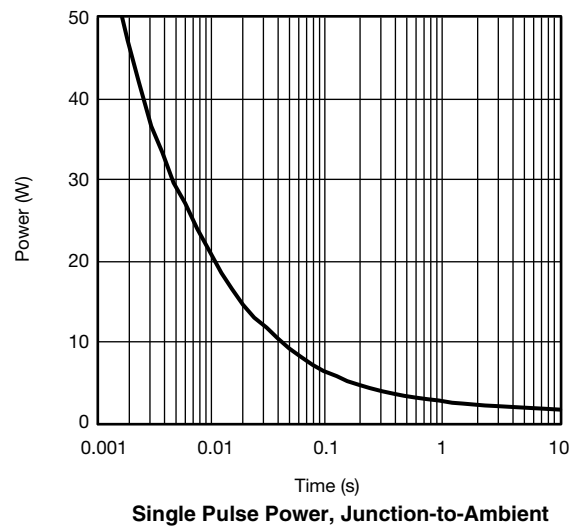
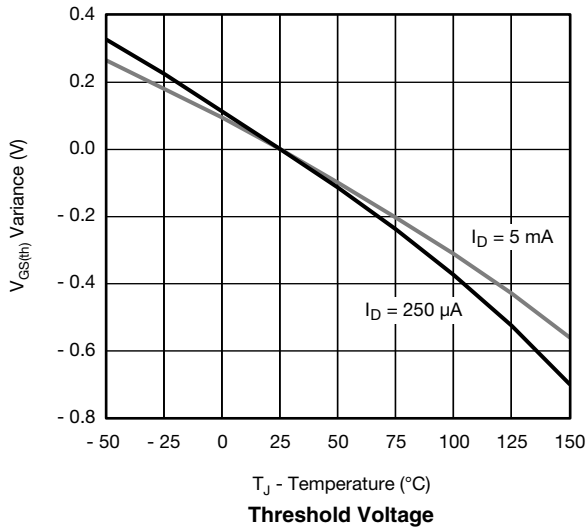
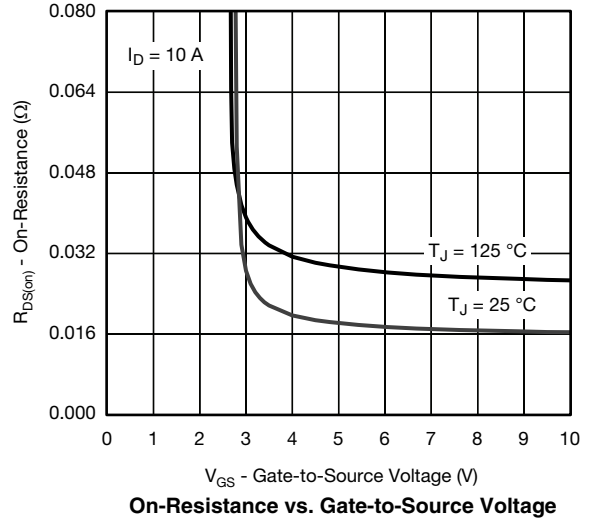
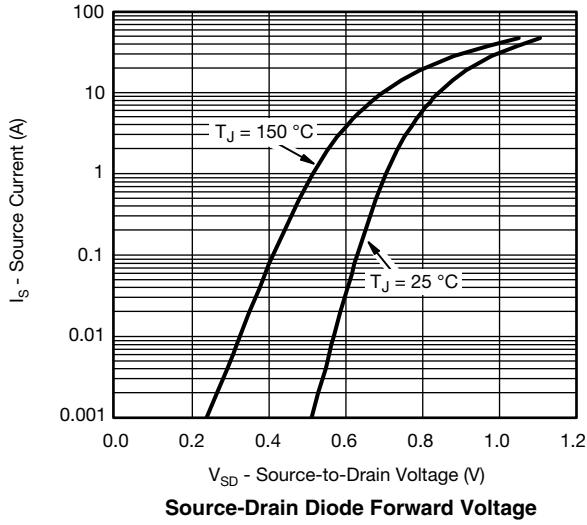


**Gate Charge**

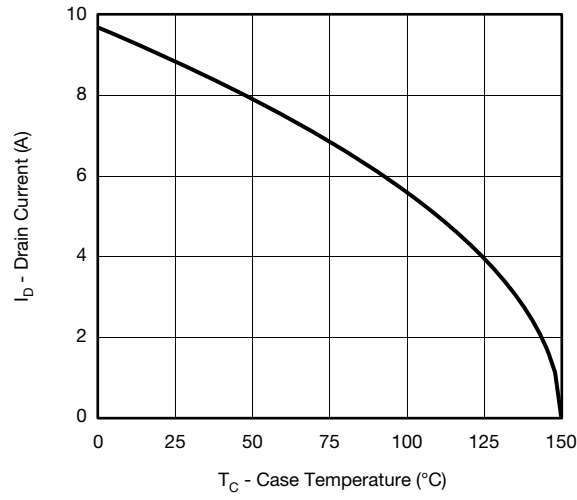


**On-Resistance vs. Junction Temperature**

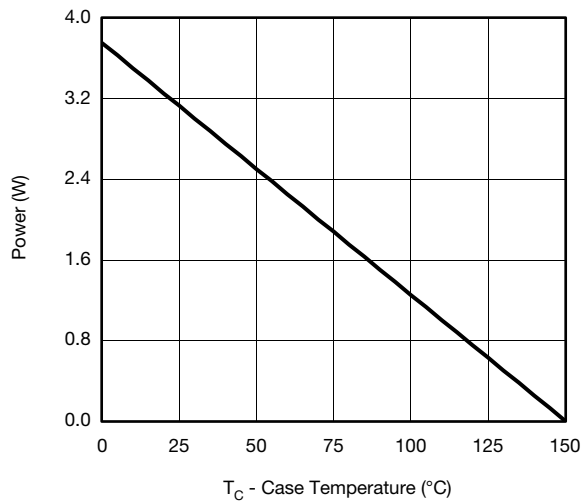
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



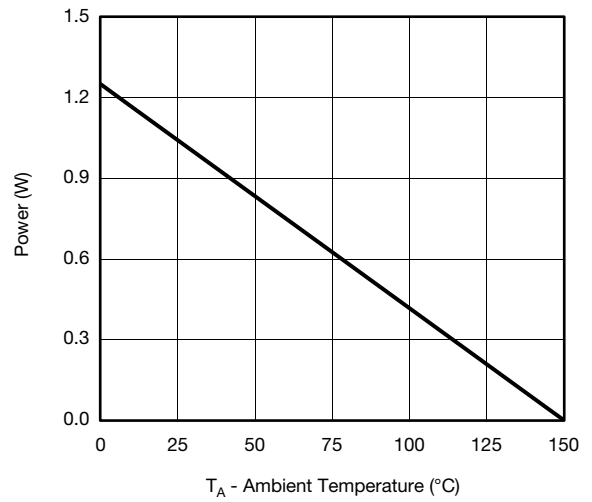
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating\***



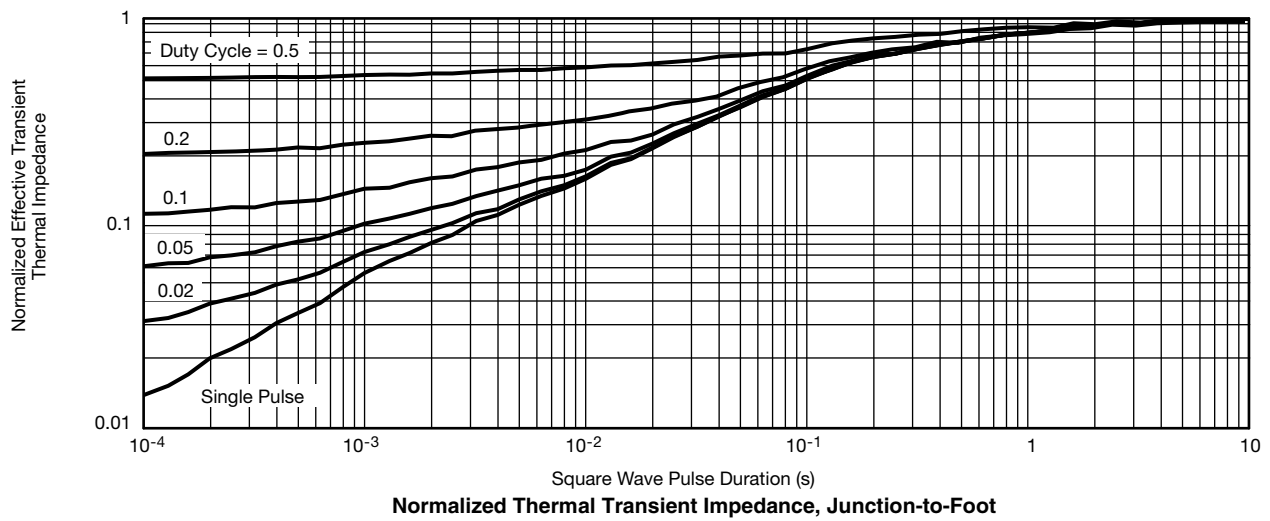
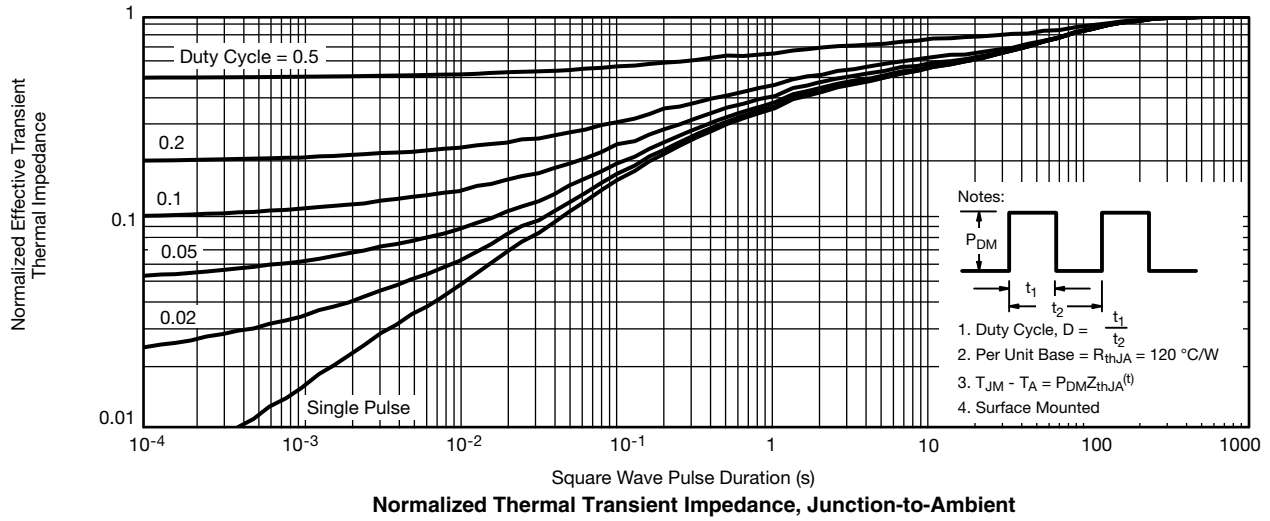
**Power Derating, Junction-to-Foot**



**Power Derating, Junction-to-Ambient**

\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

## RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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